

FROM ARMSTRONG, WESTERMAN

(MON) 2. 25' 02 13:43/ST. 13:42/NO. 4864272874 P 1

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**FACSIMILE TRANSMISSION COVER SHEET**

DATE: February 25, 2002

TO: Examiner Jack Chen  
Group Art Unit: 2813

RE: Preliminary Amendment  
U.S. Patent Appln. S.N. 09/321,605  
By: SASHIDA et al.  
Our Reference: P3329-698-A990535

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TECHNOLOGY CENTER 2800

FROM: Thomas E. Brown

FAC. TEL. NO.: 703-746-3890 or 703-308-7722 or 7724

NUMBER OF PAGES (INCLUDING THIS COVER SHEET): 12

Dear Examiner Chen:

As requested by you earlier today on the telephone, attached is a copy of the Preliminary Amendment filed February 15, 2002.

**PLEASE ACKNOWLEDGE SAFE AND CLEAR RECEIPT OF ALL PAGES BEING SENT**

TEB/kas *70*

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re the Application of:

SASHIDA et al.

Serial Number: 09/321,605

Group Art Unit: 2813

Filed: May 28, 1999

Examiner: J. Chen

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING CAPACITOR

PRELIMINARY AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

February 15, 2002

Sir:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 21 as follows:

- Sub  
E1  
D1
1. (Thrice Amended) A method of manufacturing a semiconductor device comprising the steps of:
- forming a couple of impurity diffusion layers in a semiconductor substrate;
  - forming a first insulating film covering the semiconductor substrate;
  - forming a lower electrode of a capacitor on the first insulating film;
  - forming an oxide dielectric film of the capacitor on the lower electrode;